

# Index Guided AlGaInP Laser Diode

#### Overview

DL-3038-041 is index guided 635 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by a strained multiple quantum well active layer. DL-3038-041 is suitable for applications such as bar-code scanners, optical disc systems and other optical information systems.

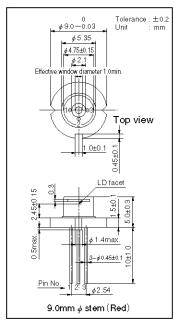
#### **Features**

Short wavelength : 635 nm (Typ.)
Low threshold current : Ith = 40 mA (Typ.)
High operating temperature : 60 °C at 5 mW
Low operating voltage : Vop = 2.2 V (Typ.)

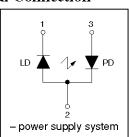
## **Absolute Maximum Ratings at Tc=25℃**

Parameter		Symbol	Ratings	Unit	
Light Output		Po	5	mW	
Reverse Voltage	Laser PIN	Vr	2 30	V	
Operating Temperature		Topr	-10 to +60	$^{\circ}\mathbb{C}$	
Storage Temperature		Tstg	-40 to +85	${\mathbb C}$	

# **Package Dimensions**



#### **Electrical Connection**

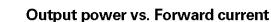


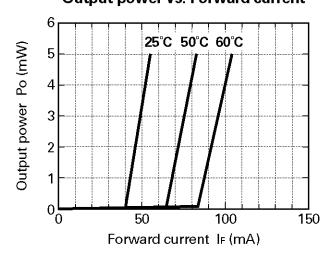
### Electrical and Optical Characteristics at Tc=25 $^{\circ}$ C

Parai	meter	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshol	d Current	Ith	CW	_	40	60	mA
Operating	g Current	Iop	Po=5mW	_	55	80	mA
Operatin	g Voltage	Vop	Po=5mW	-	2.2	2.4	V
Lasing W	avelength	λp	Po=5mW	_	635	645	nm
Beam 💥 )	Perpendicular	$\theta \perp$	Po=5mW	25	35	40	deg.
Divergence	Parallel	θ//	Po=5mW	6	8	10	deg.
Off Axis	Perpendicular	$\Delta  heta \perp$	_	_	_	±3	deg.
Angle	Parallel	$\Delta  heta$ //	_	_	-	±3	deg.
Differentia	Efficiency	dPo/dIop	_	_	0.4	_	mW/mA
Monitoring C	utput Current	Im	Po=5mW	0.05	0.15	_	mA
Astign	natism	As	Po=5mW	_	8	_	μm

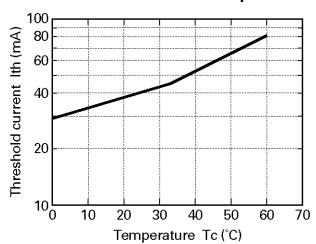
<sup>\* )</sup> Full angle at half maximum note: The above product specifications are subject to change without notice.

#### Characteristics

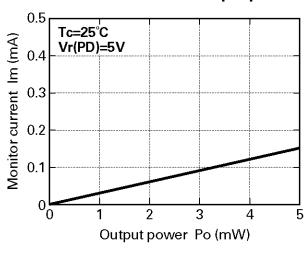




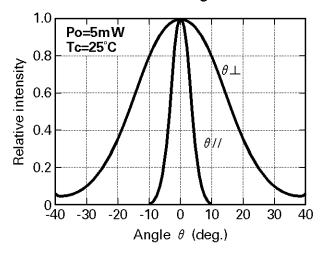
## Threshold current vs. Temperature



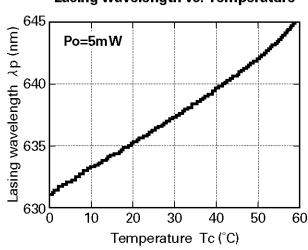
## Monitor current vs. Output power



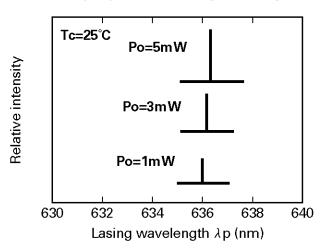
## Beam divergence



## Lasing wavelength vs. Temperature



# Output power vs. Lasing wavelength





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# Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by; Tottori SANYO Electric Co., Ltd.

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